

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-30V	60mΩ@-10V	-4.1A
	85mΩ@-4.5V	

Feature

- Advanced trench process technology
- High density cell design for ultra low on-resistance

Application

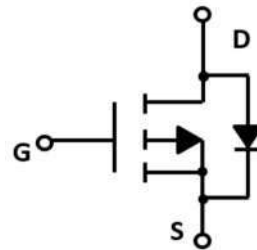
- Load Switch for Portable Devices
- DC/DC Converter

Package

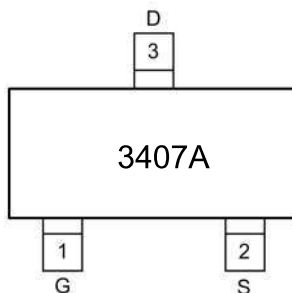


SOT-23

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	-4.1	A
Pulsed Drain Current	I _{DM}	-15	A
Power Dissipation	P _D	1.3	W
Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_A=25 °C, unless otherwise noted)

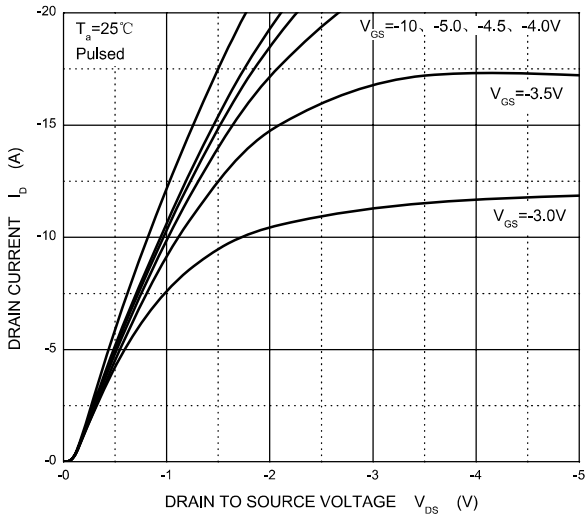
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.4	-3.0	V
Drain-source on-resistance ¹⁾	R _{DS(on)}	V _{GS} = -10V, I _D = -4.1A		48	60	mΩ
		V _{GS} = -4.5V, I _D = -3.0A		65	85	
Dynamic characteristics²⁾						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz		580		pF
Output Capacitance	C _{oss}			98		
Reverse Transfer Capacitance	C _{rss}			74		
Total Gate Charge	Q _g	V _{DS} = -15V, V _{GS} = -10V, I _D = -4.1A		6.8		nC
Gate-Source Charge	Q _{gs}			1.0		
Gate-Drain Charge	Q _{gd}			1.4		
Turn-on delay time	t _{d(on)}	V _{DD} = -15V, V _{GS} = -10V, I _D = -1A, R _{GEN} = 2.5Ω, R _L = 15Ω		14		nS
Turn-on rise time	t _r			61		
Turn-off delay time	t _{d(off)}			19		
Turn-off fall time	t _f			10		
Source-Drain Diode characteristics						
Diode Forward Current ¹⁾	I _S				-4.1	A
Diode Forward voltage	V _{DS}	V _{GS} = 0V, I _S = -4.1A			-1.2	V

Notes:

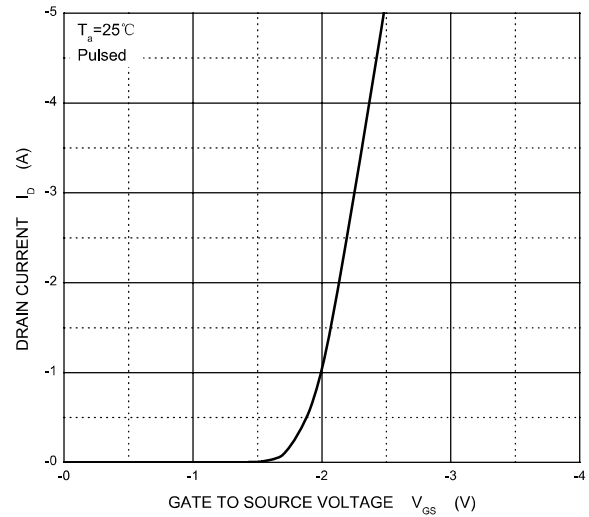
- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

Typical Characteristics

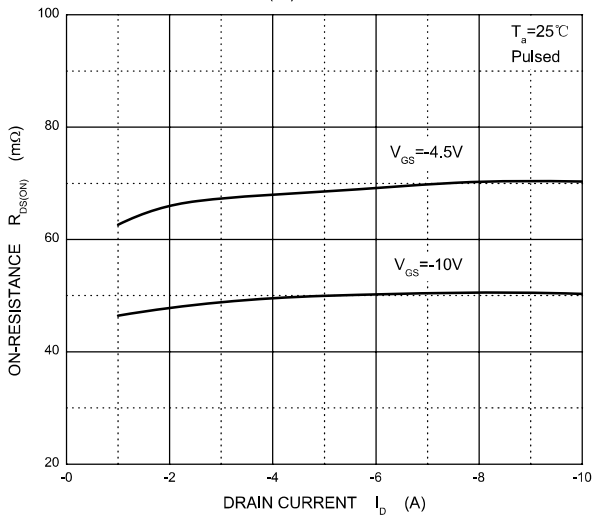
Output Characteristics



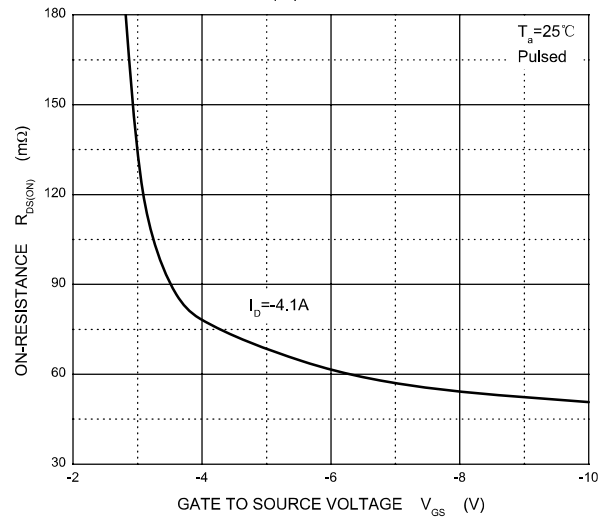
Transfer Characteristics



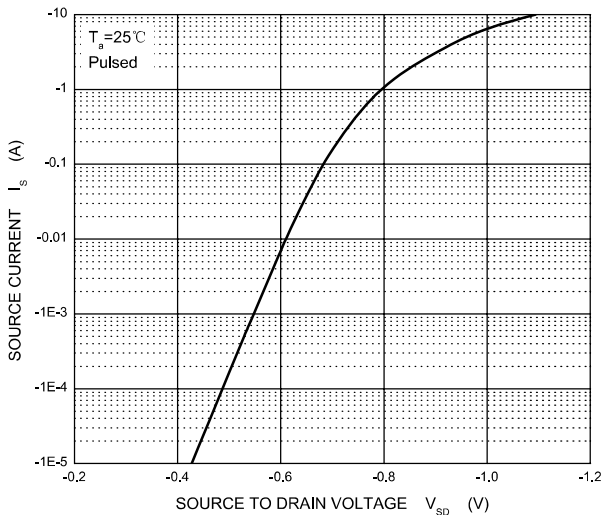
$R_{DS(ON)}$ — I_D



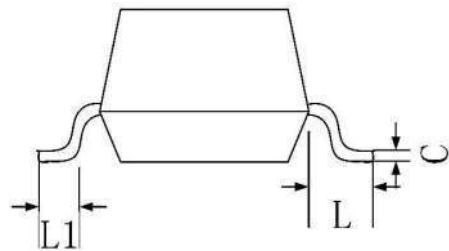
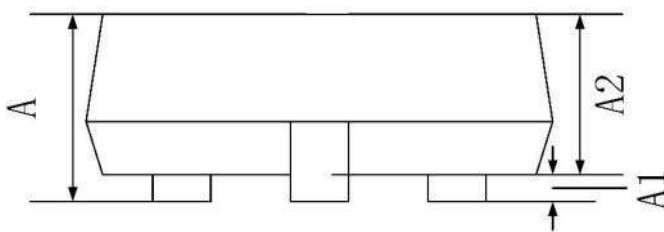
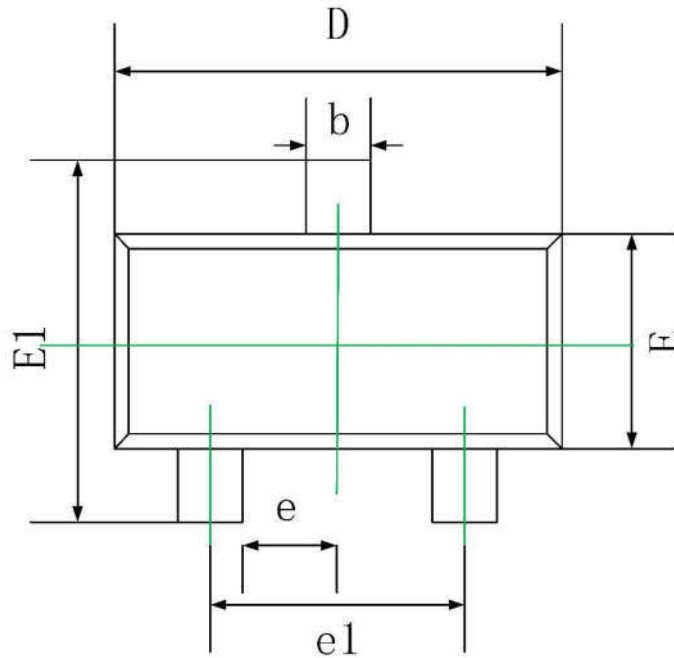
$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}



SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020

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